

20 V, P-channel Trench MOSFET

27 January 2025

**Product data sheet** 

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: Ptot = 980 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM
- AEC-Q101 qualified

### 3. Applications

- LED driver
- Power management
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-5.6	А
Static character	eristics	·		•			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 25 °C		-	27	32	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	3	
3	D	drain		G G S 017aaa259

### 6. Ordering information

Table 3. Ordering information						
Type number						
	Name	Description	Version			
PMV27UPEA	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PMV27UPEA	AE%

[1] % = placeholder for manufacturing site code

PMV27UPEA

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### 8. Limiting values

#### Table 5. Limiting values

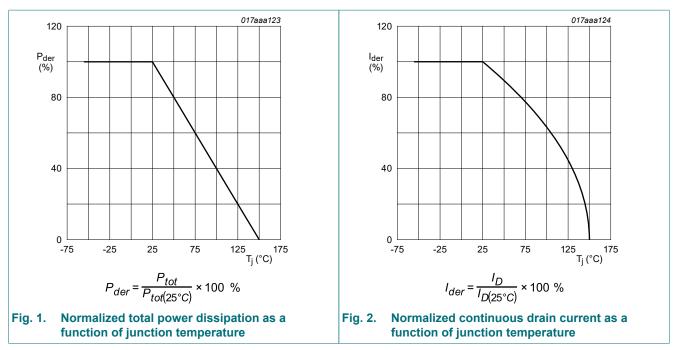
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
ID	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-5.6	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-4.5	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-2.8	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-18	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
			[1]	-	980	mW
		T <sub>sp</sub> = 25 °C		-	4150	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	I <sub>D</sub> = -1.8 A; T <sub>j(init)</sub> = 25 °C; DUT in avalanche (unclamped).		-	19	mJ
Source-drain	n diode			I		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.2	А
ESD maximu	um rating			1		
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

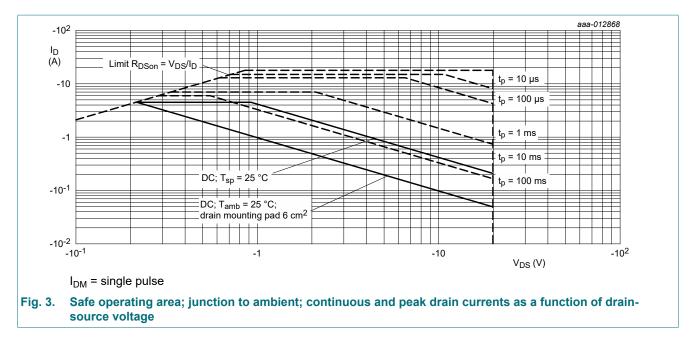
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



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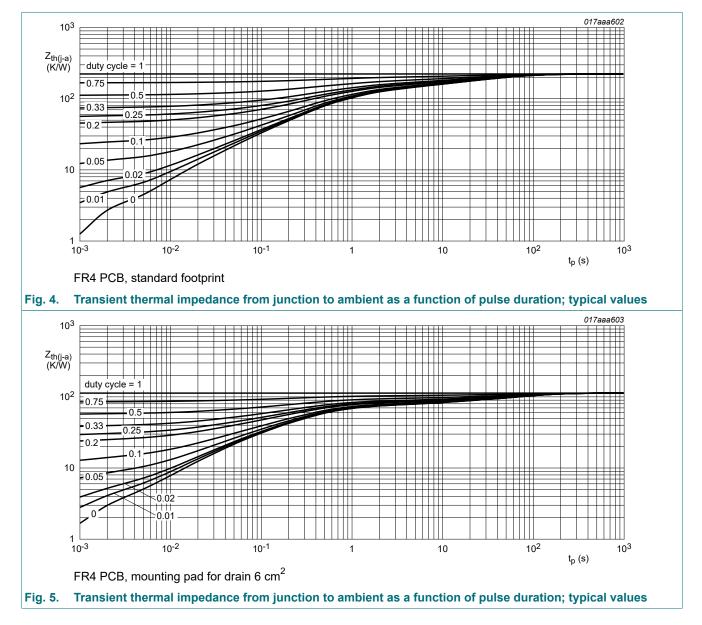
PMV27UPEA

### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	222	255	K/W
			[2]	-	111	128	K/W
		in free air; t ≤ 5 s	[2]	-	74	85	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

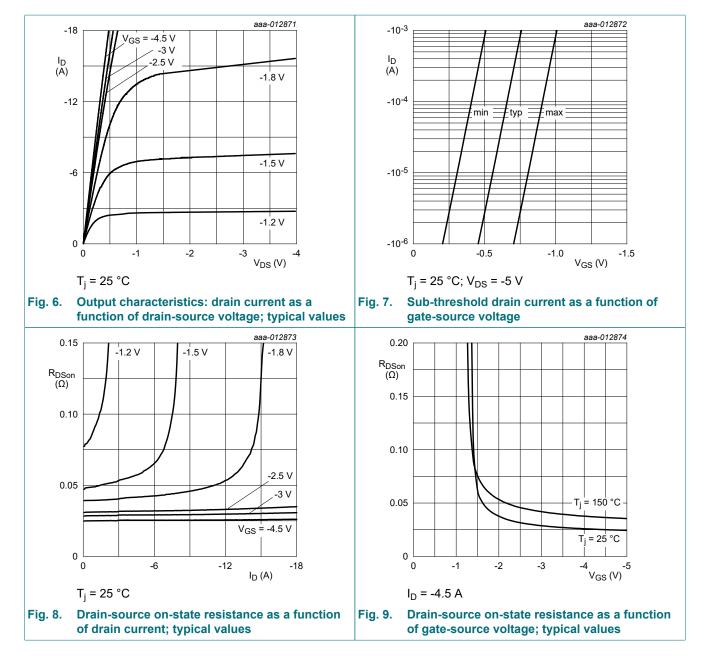
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



### **10. Characteristics**

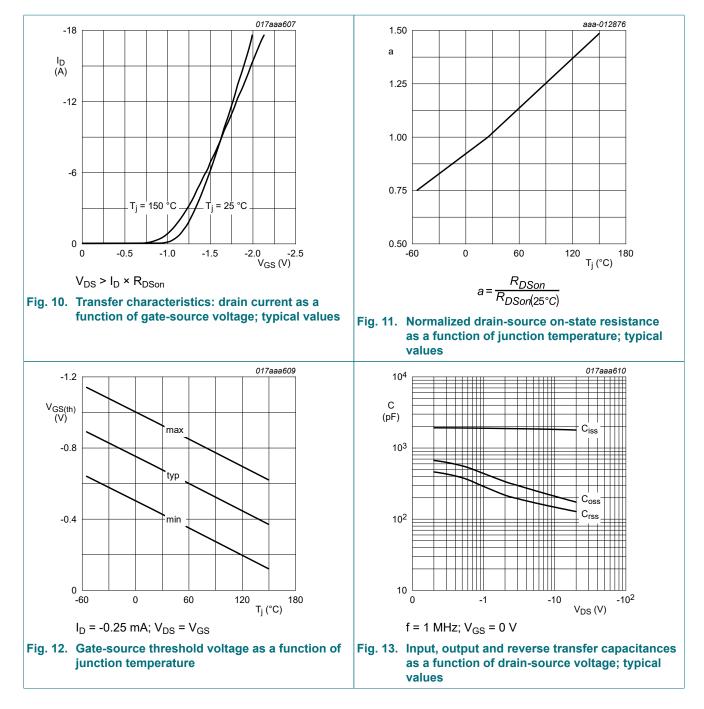
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
R <sub>DSon</sub> drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 25 °C	-	27	32	mΩ	
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 150 °C	-	40	48	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -3.8 A; T <sub>j</sub> = 25 °C	-	38	45	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -3 A; T <sub>j</sub> = 25 °C	-	50	63	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -2 A; $T_j$ = 25 °C	-	15	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	10.7	-	Ω
Dynamic ch	naracteristics	· · ·	I			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V;	-	14.7	22.1	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.6	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	2.5	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1820	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	208	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	146	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_D$ = -4.4 A; $V_{GS}$ = -4.5 V;	-	11	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	83	-	ns
t <sub>f</sub>	fall time	1	-	39	-	ns
Source-drai	in diode	· · ·				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

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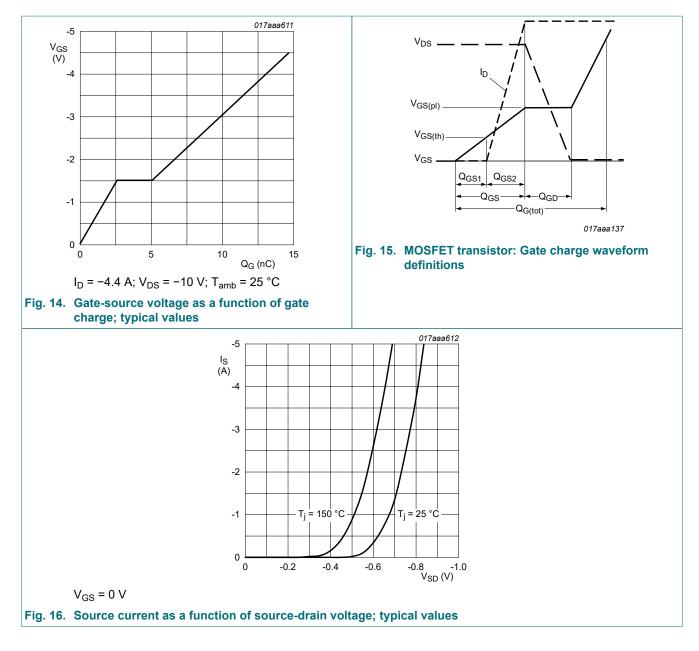


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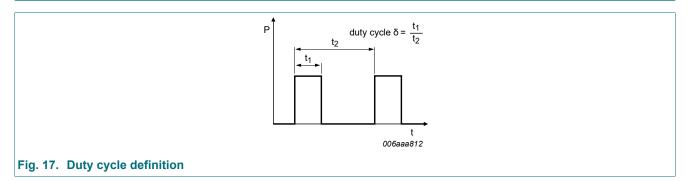


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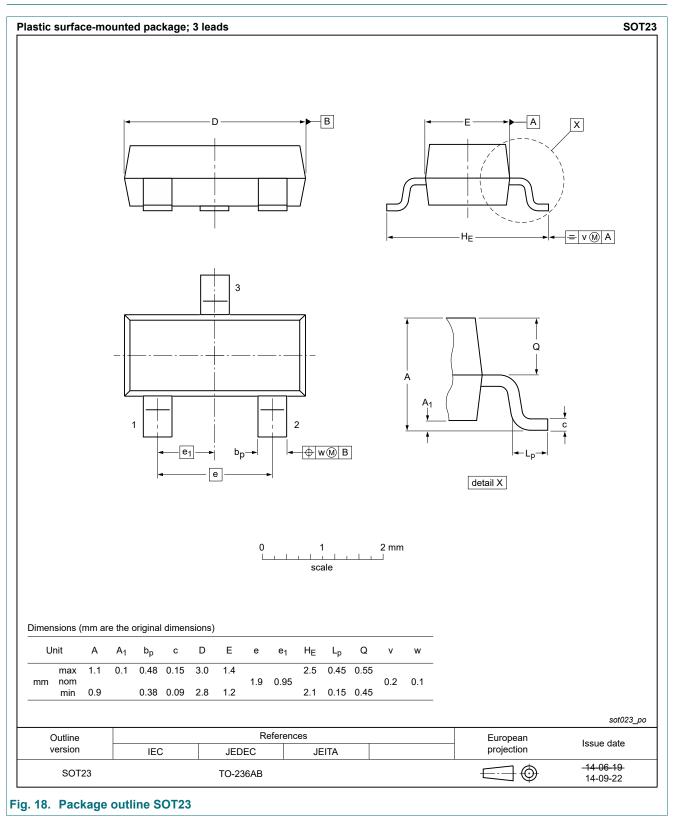
### **11. Test information**



#### **Quality information**

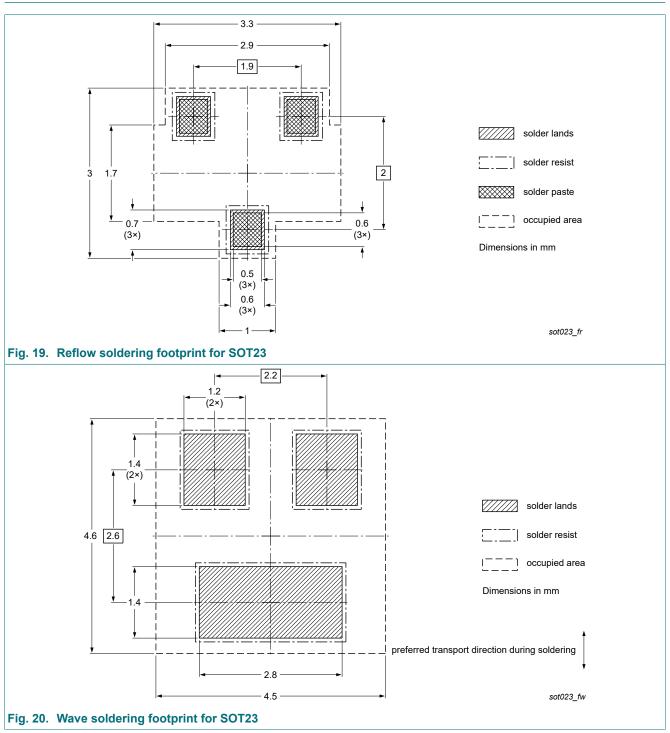
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



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### 13. Soldering



### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV27UPEA v.2	20250127	Product data sheet	-	PMV27UPEA v.1		
Modifications:	Chapter "Characteris	stics": typo correction				
PMV27UPEA v.1	20151030	Product data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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